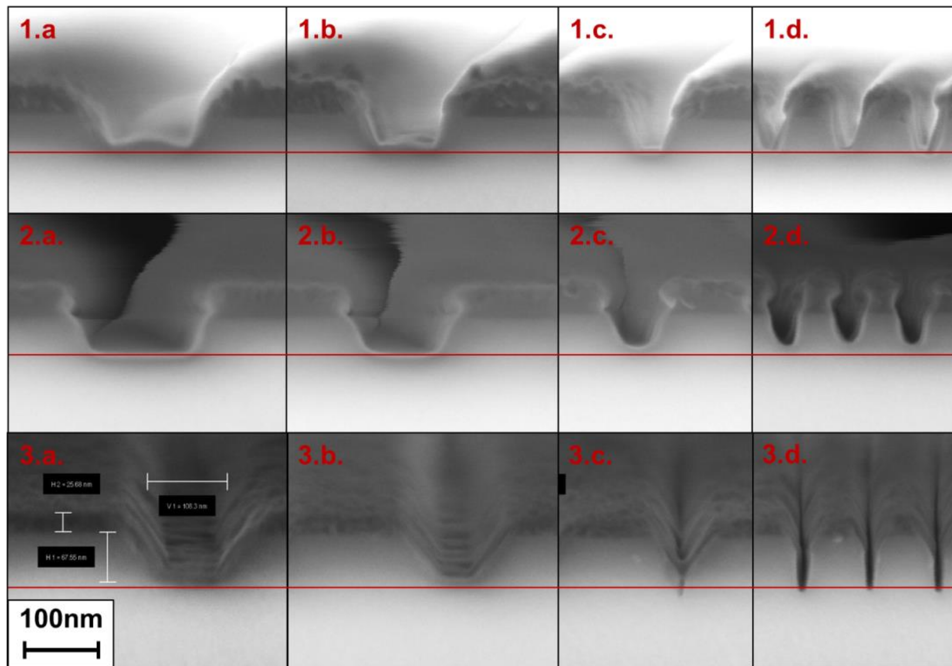

Figure 1. SEM images of evaluated silicon oxide features with varying the critical dimension. Column a: 150nm; Column b: 100nm; Column c: 60nm; Column d: 40nm). Row 1: SiO_2 features have been etched using CHF_3-based ALE. Row 2: SiO_2 has been etched with standard continues CHF_3/Ar Reactive Ion Etching. Row 3:SiO_2 features etched using CHF_3-based ALE with higher DC bias.